

Rectifying diode

RR264M-400

●Applications

General rectification

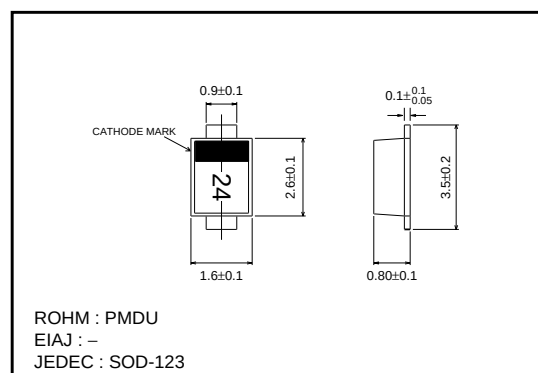
●Features

- 1) Surface mounting type. (PMDU)
- 2) Molded type.
- 3) High reliability.

●Construction

Silicon diffused junction

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_R	400	V
Forward current	I_F	1.0	A
Mean rectifying current *	I_o	0.7	A
Peak forward surge current	I_{FSM}	25	A
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~+150	°C

*1 Mounting on glass epoxy PCBs

*2 60Hz, 1cyc.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	0.94	1.10	V	$I_F=0.7mA$
Reverse current	I_R	—	0.03	10	μA	$V_R=400V$

* Please pay attention to static electricity when handling.

Diodes

●Electrical characteristic curves (Ta=25°C)

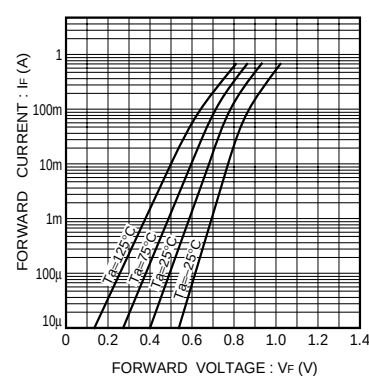


Fig. 1 Forward characteristics

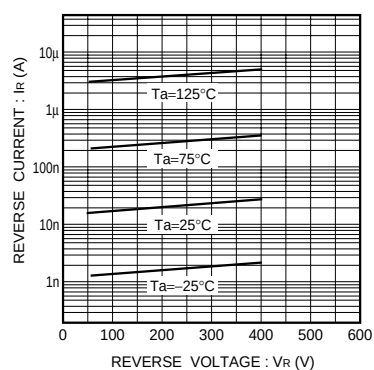


Fig. 2 Reverse characteristics

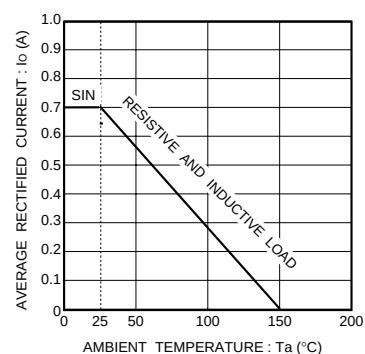


Fig. 3 Mean rectifying current characteristics

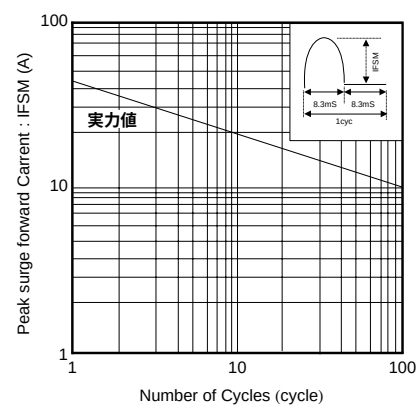


Fig. 4 Surge current characteristic

●Spice parameter

	Parameter	Value	Unit
1	IS : Saturation current	7.19E-10	A
2	N : Emission coefficient	1.6555	—
3	RS : Ohmic resistance	0.0497126	Ω
4	TT : Transit time	7.24E-06	SEC
5	CJO : Junction capacitance	1.50E-11	F
6	M : Grading coefficient	0.389542	—
7	VJ : Junction potential	0.7	V
8	FC : Depretion cap. Coefficient	0.5	—
9	EG : Activation energy	1.11	V
10	XTI : Isat temperature exponent	3	eV
11	KF : Flicker noise coefficient	—	—
12	AF : Flicker noise coefficient	—	—
13	BV : Reverse break down	400	—
14	IBV : Isat v-breakdown	0.0001	A
15	RL : Junvntional leakage resistance	1.34E+10	Ω